



Absolute Maximum Ratings

Symbol	2SC2315	2SC2316	Unit
V _{CB0}	80	100	V
V _{CEO}	60	80	V
V _{EBO}	6		V
I _C	6		A
I _B	3		A
P _C	50 (T _{FL} =25°O)		W
T _J	150		°C
T _{stg}	-55~+150		°C

Silicon NPN Triple Diffused Mesa

☆ Super Beta Transistor

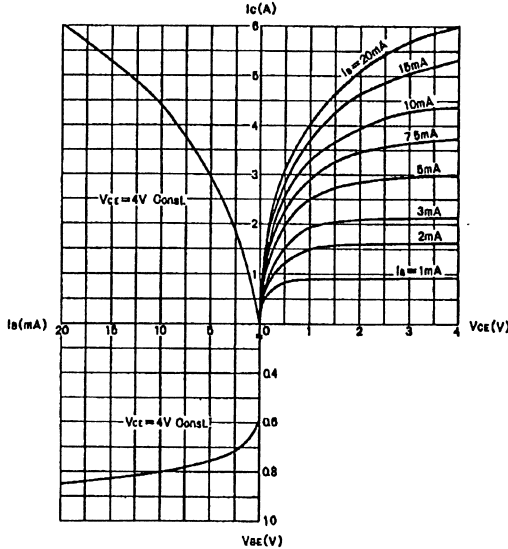
Application Example :
 General Purpose

● Outline Drawing 1MT-25(TO220)

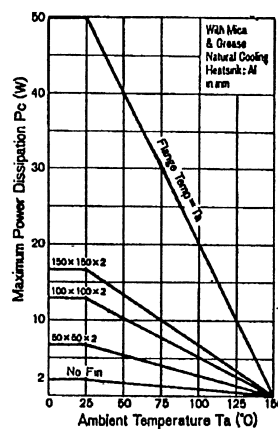
Electrical Characteristics

Symbol	Conditions	2SC2315	2SC2316	Unit
I _{CB0}	V _{CB} =	100max	100max	μA
I _{EBO}	V _{EB} =6V		1.0max	mA
V _{(BR)CEO}	I _C ≈ 25mA	60min	80min	V
h _{FE}	V _{CE} =4V, I _C =0.5A	500min		
V _{CE(sat)}	I _C ≈ 3A, I _B =0.06A	1.0max		V
f _T	V _{CE} =12V, I _E =-0.5A	30typ		MHz

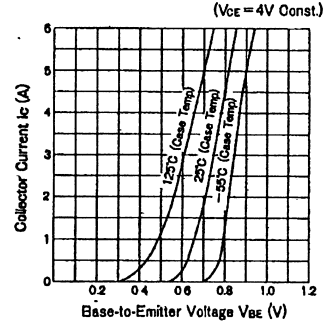
Common Emitter Characteristics (Typical Value)



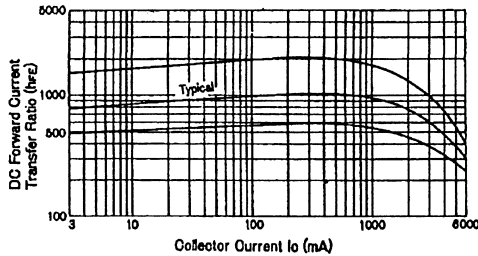
Power Derating



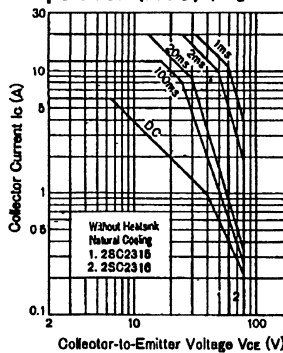
Temperature Characteristics



DC Current Gain Characteristics
 (V_{CE}=4V Const.)



Maximum Areas For Safe Operation (ASO) (Single Pulse)



Collector-to-Emitter Saturation Characteristics (Typical Value)

